

# Central<sup>TM</sup> Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

**CBR8M-L010M SERIES**

**GLASS PASSIVATED JUNCTION  
SILICON BRIDGE RECTIFIER  
8.0 AMP, 100 THRU 1000 VOLTS**

**CASE DMM**DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR8M-L010M series types are silicon single phase full wave bridge rectifiers designed for general purpose, high current applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

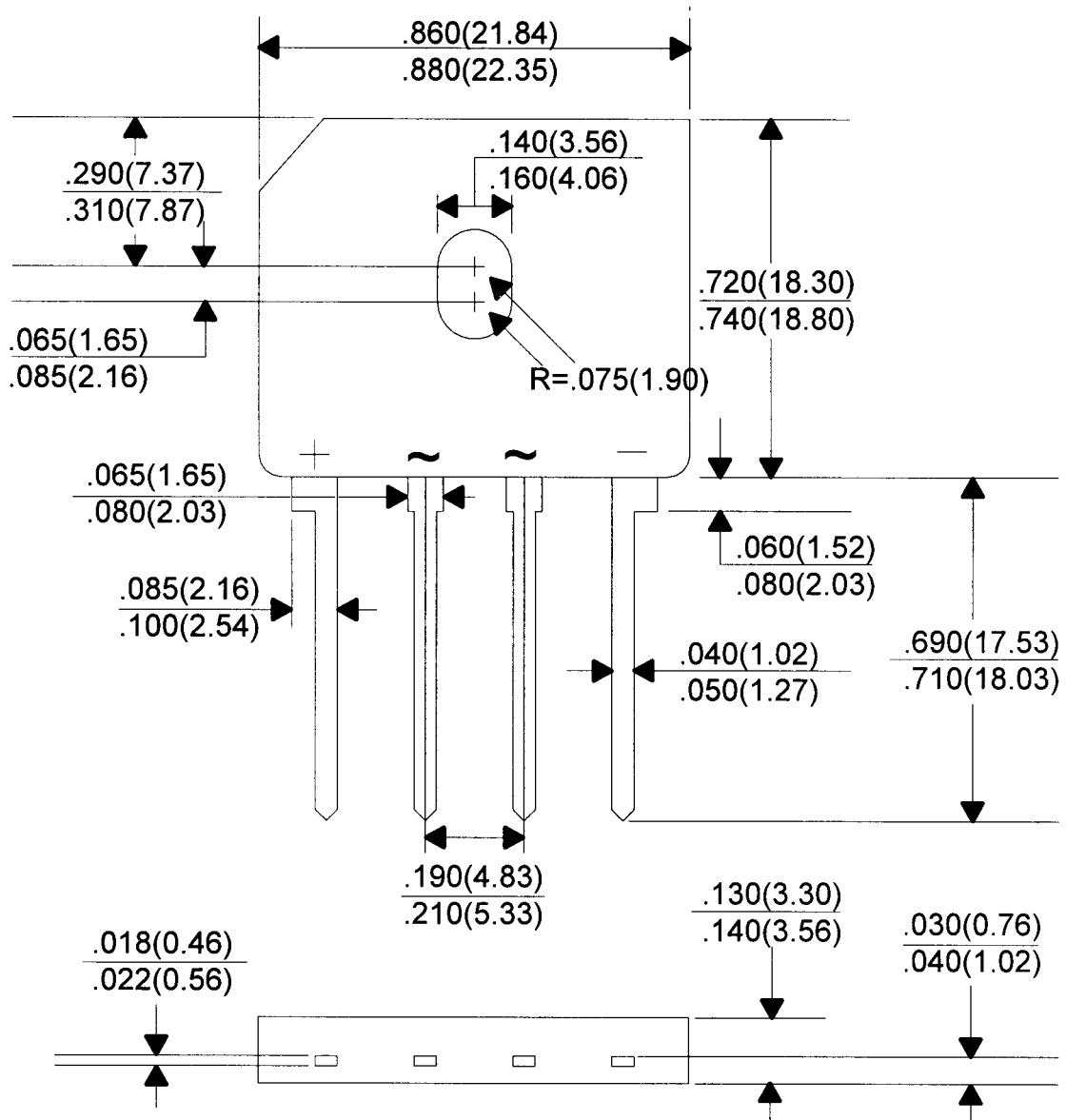
MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

	SYMBOL	CBR8M -L010M	CBR8M -L020M	CBR8M -L040M	CBR8M -L060M	CBR8M -L080M	CBR8M -L100M	UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	100	200	400	600	800	1000	V
DC Blocking Voltage	$V_R$	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ( $T_C=100^{\circ}\text{C}$ )	$I_O$				8.0			A
Peak Forward Surge Current	$I_{FSM}$				200			A
Operating and Storage								
Junction Temperature	$T_J, T_{stg}$				-65 to +150			$^{\circ}\text{C}$
Thermal Resistance	$\theta_{JC}$				3.0			$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R = \text{Rated } V_{RRM}$			5.0	$\mu\text{A}$
$I_R$	$V_R = \text{Rated } V_{RRM}, T_C=100^{\circ}\text{C}$			500	$\mu\text{A}$
$V_F$	$I_F=8.0\text{A}$			1.0	V
$C_J$	$V_R=4.0\text{V}, f=1.0\text{MHz}$		260		pF

## CASE DMM - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

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